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2-input AND gate Rev. 04 — 17 July 2007

1. General description

74HC1G08 and 74HCT1G08 are high-speed, Si-gate CMOS devices. They provide a 2-input AND function.

The HC device has CMOS input switching levels and supply voltage range 2 V to 6 V.

The HCT device has TTL input switching levels and supply voltage range 4.5 V to 5.5 V.

The standard output currents are half those of the 74HC08 and 74HCT08.

2. Features

- Symmetrical output impedance
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- SOT353-1 and SOT753 package options

3. Ordering information

Table 1.Ordering information

Type number	Package						
	Temperature range	Name	Description	Version			
74HC1G08GW	–40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads;	SOT353-1			
74HCT1G08GW			body width 1.25 mm				
74HC1G08GV	–40 °C to +125 °C	SC-74A	SC-74A plastic surface-mounted package; 5 leads				
74HCT1G08GV							

4. Marking

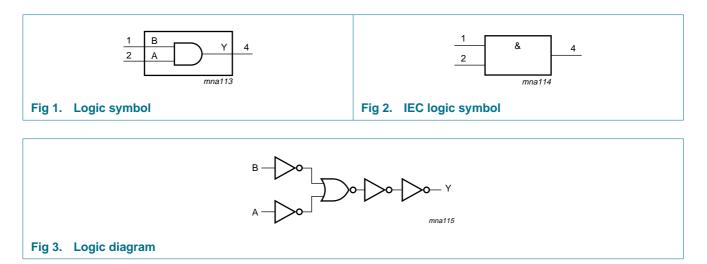
Table 2.Marking codes

Type number	Marking
74HC1G08GW	HE
74HCT1G08GW	TE
74HC1G08GV	H08
74HCT1G08GV	T08



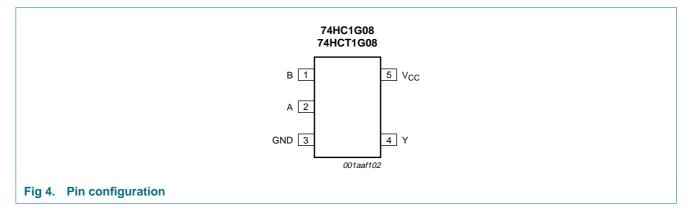
2-input AND gate

5. Functional diagram



6. Pinning information

6.1 Pinning



6.2 Pin description

Table 3.	Pin description	
Symbol	Pin	Description
В	1	data input
А	2	data input
GND	3	ground (0 V)
Y	4	data output
V _{CC}	5	supply voltage

2-input AND gate

7. Functional description

Table 4.Function table

H = HIGH voltage level; L = LOW voltage level

Input		Output
Α	В	Y
L	L	L
L	Н	L
Н	L	L
Н	Н	Н

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V). [1]

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+7.0	V
I _{IK}	input clamping current	$V_{\rm I}$ < -0.5 V or $V_{\rm I}$ > $V_{\rm CC}$ + 0.5 V	-	±20	mA
I _{OK}	output clamping current	$V_{\rm O}$ < –0.5 V or $V_{\rm O}$ > $V_{\rm CC}$ + 0.5 V	-	±20	mA
I _O	output current	$-0.5 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{CC}} + 0.5 \text{ V}$	-	±12.5	mA
I _{CC}	supply current		-	25	mA
I _{GND}	ground current		-25	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 \ ^{\circ}C \ to +125 \ ^{\circ}C$	[2] _	200	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] Above 55 °C the value of P_{tot} derates linearly with 2.5 mW/K.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	74HC1G08			74HCT1G08			Unit
			Min	Тур	Max	Min	Тур	Max	
V _{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
VI	input voltage		0	-	V_{CC}	0	-	V_{CC}	V
Vo	output voltage		0	-	V_{CC}	0	-	V_{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
$\Delta t / \Delta V$	input transition rise and fall rate	$V_{CC} = 2.0 V$	-	-	625	-	-	-	ns/V
		$V_{CC} = 4.5 V$	-	-	139	-	-	139	ns/V
		$V_{CC} = 6.0 V$	-	-	83	-	-	-	ns/V

2-input AND gate

10. Static characteristics

Table 7. Static characteristics

Voltages are referenced to GND (ground = 0 V). All typical values are measured at T_{amb} = 25 °C.

Symbol	Parameter	rameter Conditions		–40 °C to +85 °C			–40 °C to +125 °C		
			Min	Тур	Max	Min	Max		
For type	74HC1G08								
VIH	HIGH-level input	$V_{CC} = 2.0 V$	1.5	1.2	-	1.5	-	V	
voltage		$V_{CC} = 4.5 V$	3.15	2.4	-	3.15	-	V	
		$V_{CC} = 6.0 V$	4.2	3.2	-	4.2	-	V	
V _{IL}	LOW-level input	$V_{CC} = 2.0 V$	-	0.8	0.5	-	0.5	V	
	voltage	$V_{CC} = 4.5 V$	-	2.1	1.35	-	1.35	V	
		$V_{CC} = 6.0 V$	-	2.8	1.8	-	1.8	V	
V _{OH}	HIGH-level output	$V_{I} = V_{IH} \text{ or } V_{IL}$							
	voltage	$I_{O} = -20 \ \mu A; \ V_{CC} = 2.0 \ V$	1.9	2.0	-	1.9	-	V	
		$I_O = -20 \ \mu\text{A}; \ V_{CC} = 4.5 \ \text{V}$	4.4	4.5	-	4.4	-	V	
		I_O = –20 $\mu\text{A};V_{CC}$ = 6.0 V	5.9	6.0	-	5.9	-	V	
		I_{O} = -2.0 mA; V_{CC} = 4.5 V	4.13	4.32	-	3.7	-	V	
		$I_{O} = -2.6 \text{ mA}; V_{CC} = 6.0 \text{ V}$	5.63	5.81	-	5.2	-	V	
V _{OL}	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$							
		$I_{O} = 20 \ \mu A; \ V_{CC} = 2.0 \ V$	-	0	0.1	-	0.1	V	
		$I_{O} = 20 \ \mu A; \ V_{CC} = 4.5 \ V$	-	0	0.1	-	0.1	V	
		$I_{O} = 20 \ \mu A; \ V_{CC} = 6.0 \ V$	-	0	0.1	-	0.1	V	
		I_{O} = 2.0 mA; V_{CC} = 4.5 V	-	0.15	0.33	-	0.4	V	
		I_{O} = 2.6 mA; V_{CC} = 6.0 V	-	0.16	0.33	-	0.4	V	
lı	input leakage current	$V_{I} = V_{CC}$ or GND; $V_{CC} = 6.0$ V	-	-	1.0	-	1.0	μA	
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 6.0$ V	-	-	10	-	20	μA	
Cı	input capacitance		-	1.5	-	-	-	pF	
For type	74HCT1G08								
VIH	HIGH-level input voltage	V_{CC} = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	V	
V _{IL}	LOW-level input voltage	V_{CC} = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	V	
V _{ОН}	HIGH-level output	$V_{I} = V_{IH} \text{ or } V_{IL}$							
	voltage	$I_{O} = -20 \ \mu A; \ V_{CC} = 4.5 \ V$	4.4	4.5	-	4.4	-	V	
		I_{O} = -2.0 mA; V_{CC} = 4.5 V	4.13	4.32	-	3.7	-	V	
V _{OL}	LOW-level output	$V_{I} = V_{IH} \text{ or } V_{IL}$							
	voltage	I_{O} = 20 µA; V_{CC} = 4.5 V	-	0	0.1	-	0.1	V	
		I_{O} = 2.0 mA; V_{CC} = 4.5 V	-	0.15	0.33	-	0.4	V	
l	input leakage current	$V_{I} = V_{CC}$ or GND; $V_{CC} = 5.5$ V	-	-	1.0	-	1.0	μΑ	

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Voltages a	re referenced to GND (g	ground = 0 V). All typical values are	measur	ed at T _a	amb = 25	° <i>C.</i>		
Symbol	Parameter	Conditions	–40 °C to +85 °C			_40 °C t	Unit	
			Min	Тур	Max	Min	Max	
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5$ V	-	-	10	-	20	μA
ΔI_{CC}	additional supply current	per input; V _{CC} = 4.5 V to 5.5 V; V _I = V _{CC} - 2.1 V; I _O = 0 A	-	-	500	-	850	μΑ
CI	input capacitance		-	1.5	-	-	-	pF

Table 7. Static characteristics ... continued

11. Dynamic characteristics

Table 8. Dynamic characteristics

GND = 0 V; $t_r = t_f \le 6.0$ ns; All typical values are measured at $T_{amb} = 25 \degree C$. For test circuit see Figure 6

Symbol	Parameter	Conditions		−40 °C to +85 °C			_40 °C t	Unit	
				Min	Тур	Max	Min	Max	
For type	74HC1G08	'							
t _{pd}	propagation delay	A and B to Y; see Figure 5	<u>[1]</u>						
		$V_{CC} = 2.0 \text{ V}; \text{ C}_{L} = 50 \text{ pF}$		-	25	115	-	135	ns
		$V_{CC} = 4.5 \text{ V}; \text{ C}_{L} = 50 \text{ pF}$		-	9	23	-	27	ns
		$V_{CC} = 5.0 \text{ V}; \text{ C}_{L} = 15 \text{ pF}$		-	7	-	-	-	ns
		$V_{CC} = 6.0 \text{ V}; \text{ C}_{L} = 50 \text{ pF}$		-	8	20	-	23	ns
C _{PD}	power dissipation capacitance	$V_I = GND$ to V_{CC}	[2]	-	19	-	-	-	pF
For type	74HCT1G08								
t _{pd}	propagation delay	A and B to Y; see Figure 5	[1]						
		$V_{CC} = 4.5 \text{ V}; \text{ C}_{L} = 50 \text{ pF}$		-	11	23	-	27	ns
		$V_{CC} = 5.0 \text{ V}; \text{ C}_{L} = 15 \text{ pF}$		-	11	-	-	-	ns
C _{PD}	power dissipation capacitance	$V_I = GND$ to $V_{CC} - 1.5$ V	[2]	-	21	-	-	-	pF

[1] t_{pd} is the same as t_{PLH} and t_{PHL} .

[2] C_{PD} is used to determine the dynamic power dissipation P_D (μ W).

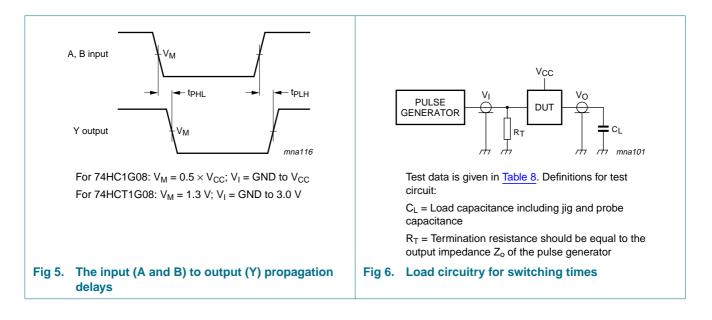
$$\begin{split} P_{D} &= C_{PD} \times V_{CC}^{2} \times f_{i} + \sum \left(C_{L} \times V_{CC}^{2} \times f_{o} \right) \text{ where:} \\ f_{i} &= \text{input frequency in MHz} \\ f_{o} &= \text{output frequency in MHz} \\ C_{L} &= \text{output load capacitance in pF} \end{split}$$

 $C_{\rm L}$ = output load capacitance in pi

$$\begin{split} V_{CC} &= \text{supply voltage in Volts} \\ \Sigma \; (C_L \times V_{CC}{}^2 \times f_o) = \text{sum of outputs} \end{split}$$

2-input AND gate

12. Waveforms



2-input AND gate

13. Package outline

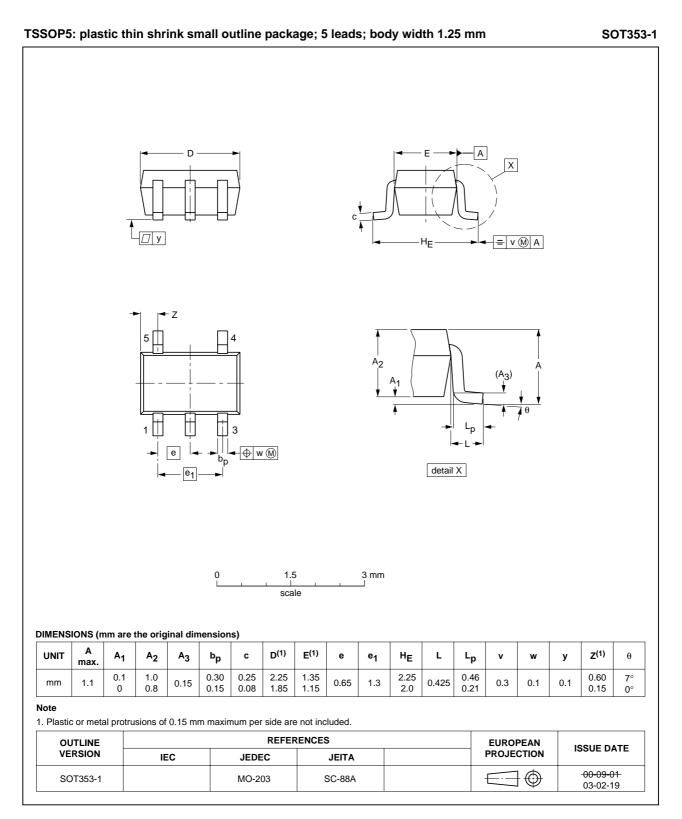


Fig 7. Package outline SOT353-1 (TSSOP5)

2-input AND gate

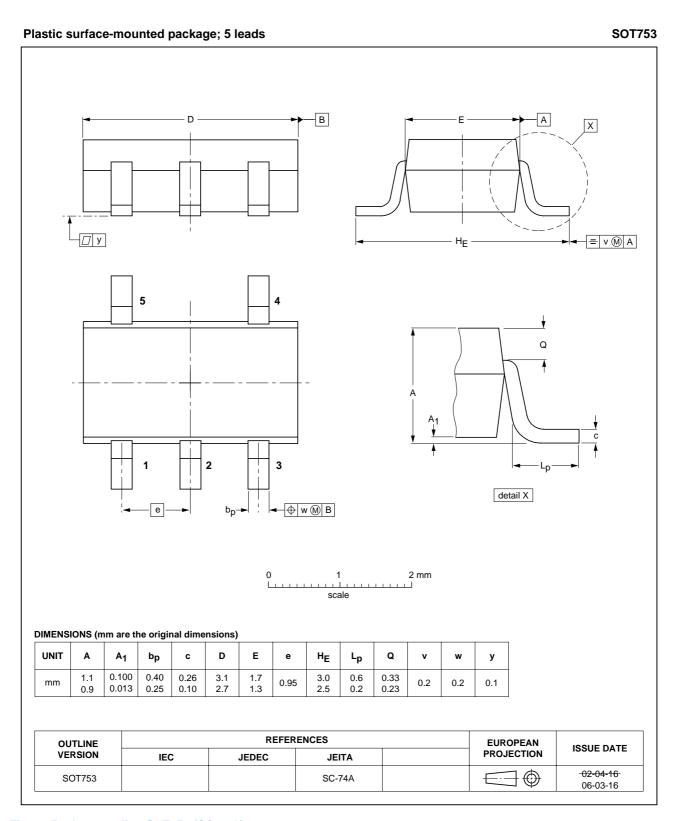


Fig 8. Package outline SOT753 (SC-74A)

14. Abbreviations

Table 9.	Abbreviations		
Acronym	Description		
DUT	Device Under Test		
TTL	Transistor-Transistor Logic		

15. Revision history

Table 10.Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes			
74HC_HCT1G08_4	20070717	Product data sheet	-	74HC_HCT1G08_3			
Modifications:		of this data sheet has been re of NXP Semiconductors.	edesigned to comply v	vith the new identity			
	 Legal texts 	have been adapted to the new	v company name whe	ere appropriate.			
	 Package S0 	OT353 changed to SOT353-1	in <u>Table 1</u> and <u>Figure</u>	<u>7</u> .			
	 Quick Reference Data and Soldering sections removed. 						
	 Section 2 "F 	Features" updated.					
74HC_HCT1G08_3	20020517	Product specification	-	74HC_HCT1G08_2			
74HC_HCT1G08_2	20010302	Product specification	-	74HC_HCT1G08_1			
74HC_HCT1G08_1	19981110	Preliminary specification	-	-			

16. Legal information

16.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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NXP Semiconductors

74HC1G08; 74HCT1G08

2-input AND gate

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